Supporting information

Reducing the contact and channel resistances of black phosphorus via low-temperature vacuum annealing

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Figure S1 (a) micro-Raman spectra and (b) intensity ratio \( \frac{A_g}{A_g^2} \) of BP vacuum-annealed at different temperatures.
Figure S2 (a) $\mu_{FE}$ and on/off ratio of BP FETs vacuum-annealed at different temperatures